## "Yب / Descriptions

TO-220 N MOS

N-CHANNEL MOSFET in a TO-220 Plastic Package.

## ◕ È / Features

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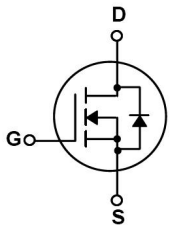
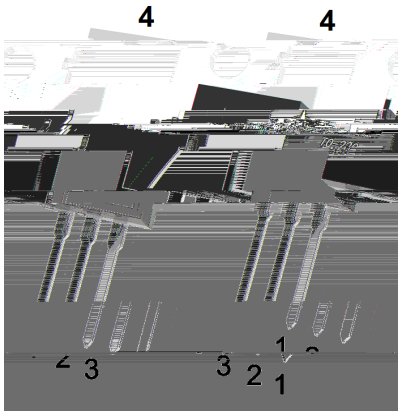
Low gate charge, low crss, fast switching, HF Product.

## [redacted]

DC/DC

These devices are well suited for high efficiency switching DC/DC converters, and switch mode power supplies.




PIN1 G PIN 2 4 D PIN 3 S

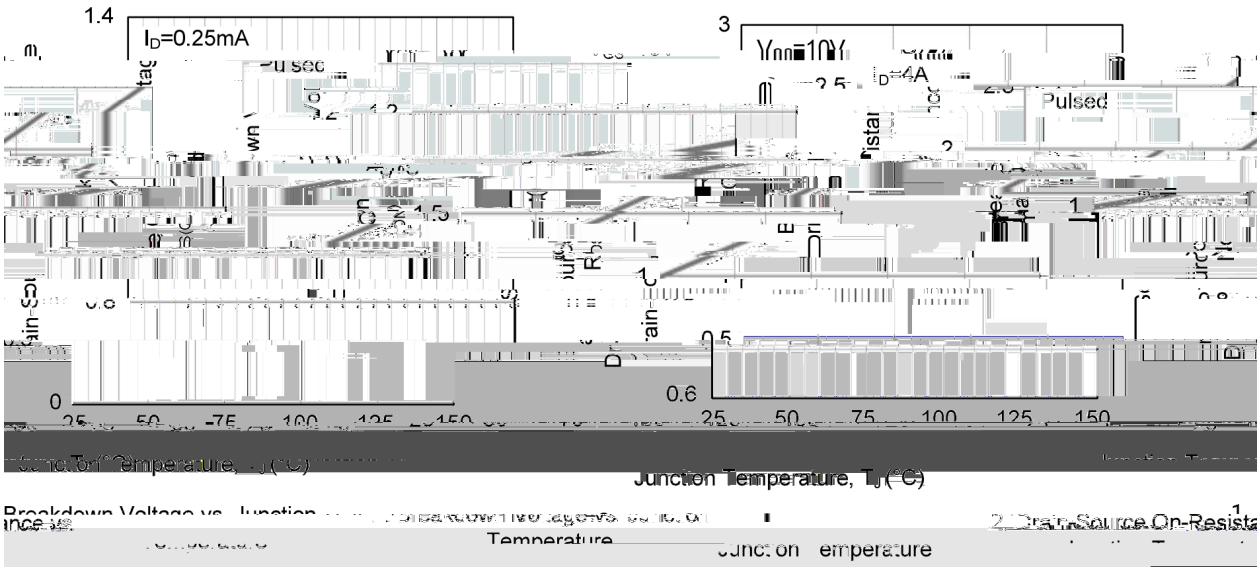
## ł. ʜ ɔ̀ / Marking

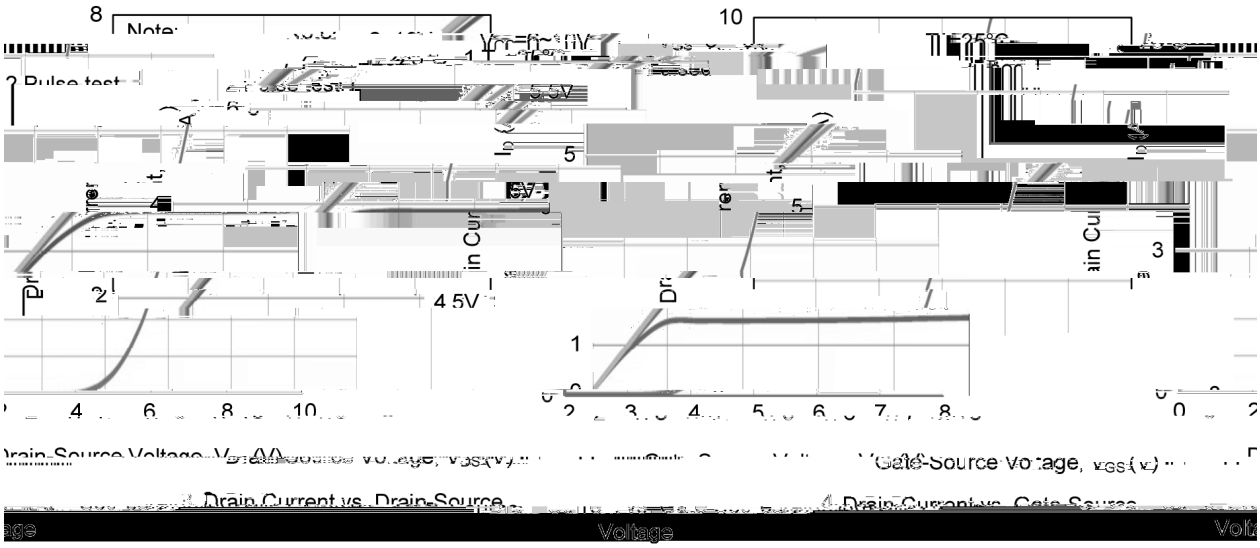
See Marking Instructions.

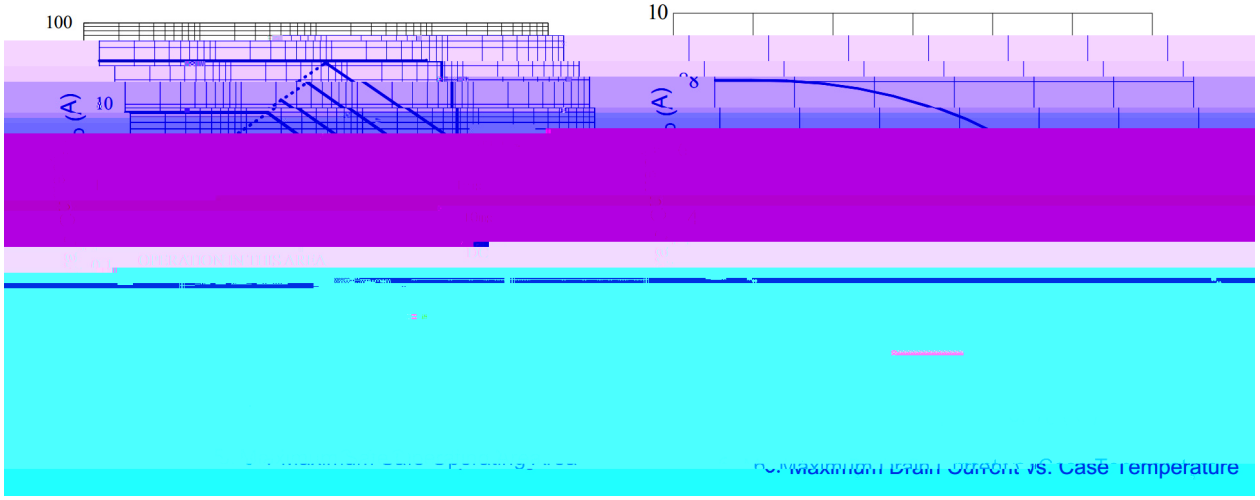
| Parameter | Symbol | Rating | Unit |
|---|---|---|---|
| Drain-Source Voltage | $V_{DSS}$ | 650 | V |
| Drain Current | $I_D$(Tc=25 ) | 8 | A |
| Drain Current - Pulsed | $I_{DM}$ | 32 | A |
| Gate-Source Voltage | $V_{GSS}$ | ±30 | V |
| Single Pulsed Avalanche Energy | $E_{AS}$ | 597 | mJ |
| Avalanche Current | $I_{AR}$ | 10.5 | A |
| Power Dissipation | $P_D$(Tc=25 ) | 110 | W |
| Operating and Storage Temperature Range | $T_J$,$T_{STG}$ | -55 to 150 | |
| Thermal resistance, junction- case | $R_{dJC}$ | 1.14 | /W |

| Parameter | Symbol | Test Conditions | Min | Typ | Max | Unit |
|---|---|---|---|---|---|---|
| Drain-Source Breakdown Voltage | $BV_{DSS}$ | $V_{GS}$=0V $I_D$=250εA | 650 | 700 | | V |
| Zero Gate Voltage Drain Current | $I_{DSS}$ | $V_{DS}$=650V $V_{GS}$=0V | | | 1.0 | εA |
| Gate-Body Leakage Current, Forward | $I_{GSS}$ | $V_{GS}$GSj10.4955 354.5.9 395.7803 Tm1.4429 T5(GS)Tj.48 .0005 Tc1. | | | | |

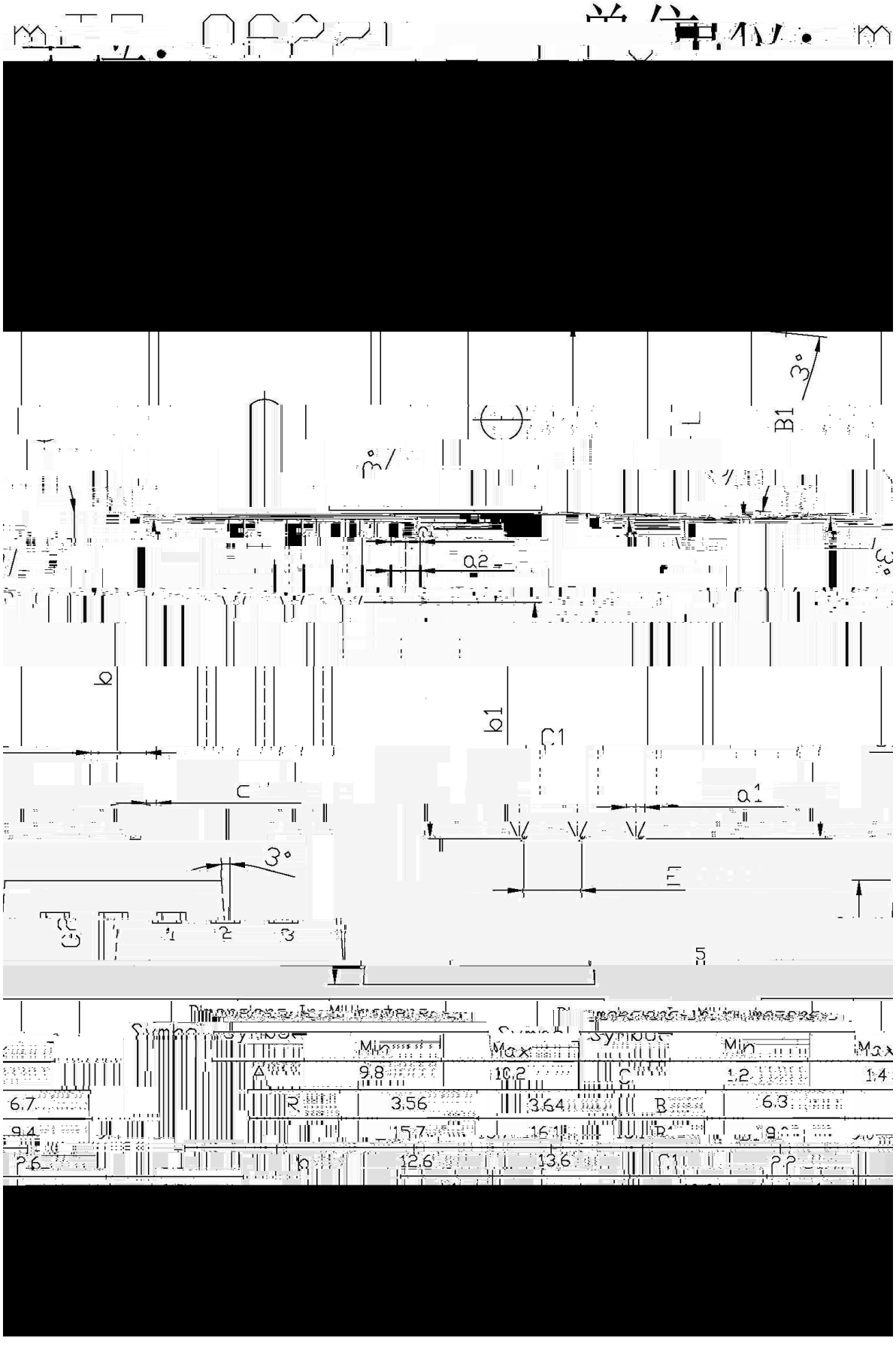
## ≠ Ǝ ̃Ą ´E ∀ ƒ / Electrical Characteristic Curve



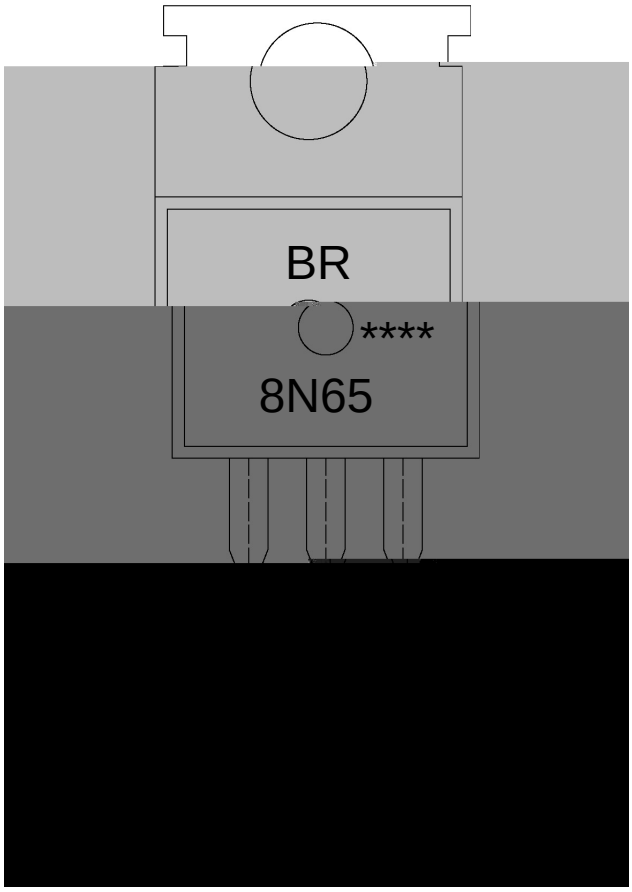



## ᵘ Ė Ò Ļ ƒ / Package Dimensions



## ł. Ļ'Ω / Marking Instructions




BR

8N65

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Note:

| | |
|---|---|
| BR: | Company Code |
| 8N65: | Product Type Code |
| ****: | Lot No. Code, code change with Lot No |

## ↓ ș ╕ ẘ ´E ᛋ ƒ (ᾠ ᴈ) / Temperature Profile for Dip Soldering(Pb-Free)